

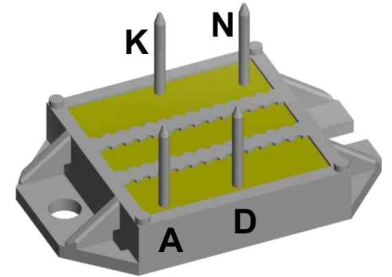
# HiPerFRED Module

$V_{RRM} = 1200\text{ V}$   
 $I_{DAV} = 32\text{ A}$   
 $t_{rr} = 40\text{ ns}$

High Performance Fast Recovery Diode  
 Low Loss and Soft Recovery  
 1~ Rectifier Bridge

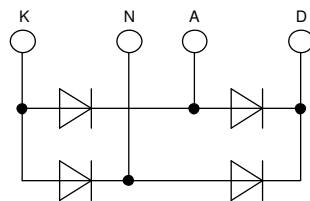
Part number

**VBE26-12NO7**



Backside: isolated

 E72873



## Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

## Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

## Package: ECO-PAC1

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

## Disclaimer Notice

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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1200	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1200	V
$I_R$	reverse current, drain current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^\circ\text{C}$			100	$\mu\text{A}$
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^\circ\text{C}$			0.5	mA
$V_F$	forward voltage drop	$I_F = 15\text{ A}$	$T_{VJ} = 25^\circ\text{C}$			2.73	V
		$I_F = 30\text{ A}$				3.20	V
		$I_F = 15\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.75	V
		$I_F = 30\text{ A}$				2.20	V
$I_{DAV}$	bridge output current	$T_C = 85^\circ\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 150^\circ\text{C}$			32	A
$V_{FO}$	threshold voltage	} for power loss calculation only				1.32	V
$r_F$	slope resistance					30	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					1.6	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.30		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		80	W
$I_{FSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^\circ\text{C}$			90	A
$C_J$	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		7		pF
$I_{RM}$	max. reverse recovery current	} $I_F = 15\text{ A}; V_R = 600\text{ V}$ $-di_F/dt = 200\text{ A}/\mu\text{s}$		$T_{VJ} = 25^\circ\text{C}$		6	A
				$T_{VJ} = 100^\circ\text{C}$		9	A
$t_{rr}$	reverse recovery time			$T_{VJ} = 25^\circ\text{C}$		40	ns
				$T_{VJ} = 100^\circ\text{C}$		135	ns



Package ECO-PAC1		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			100	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				19		g
$M_D$	mounting torque		1.4		2	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	10.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VBE26-12NO7	VBE26-12NO7	Box	25	482366

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^{\circ}C$

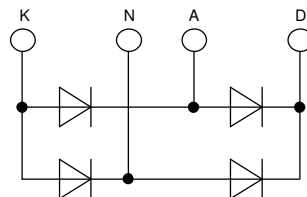
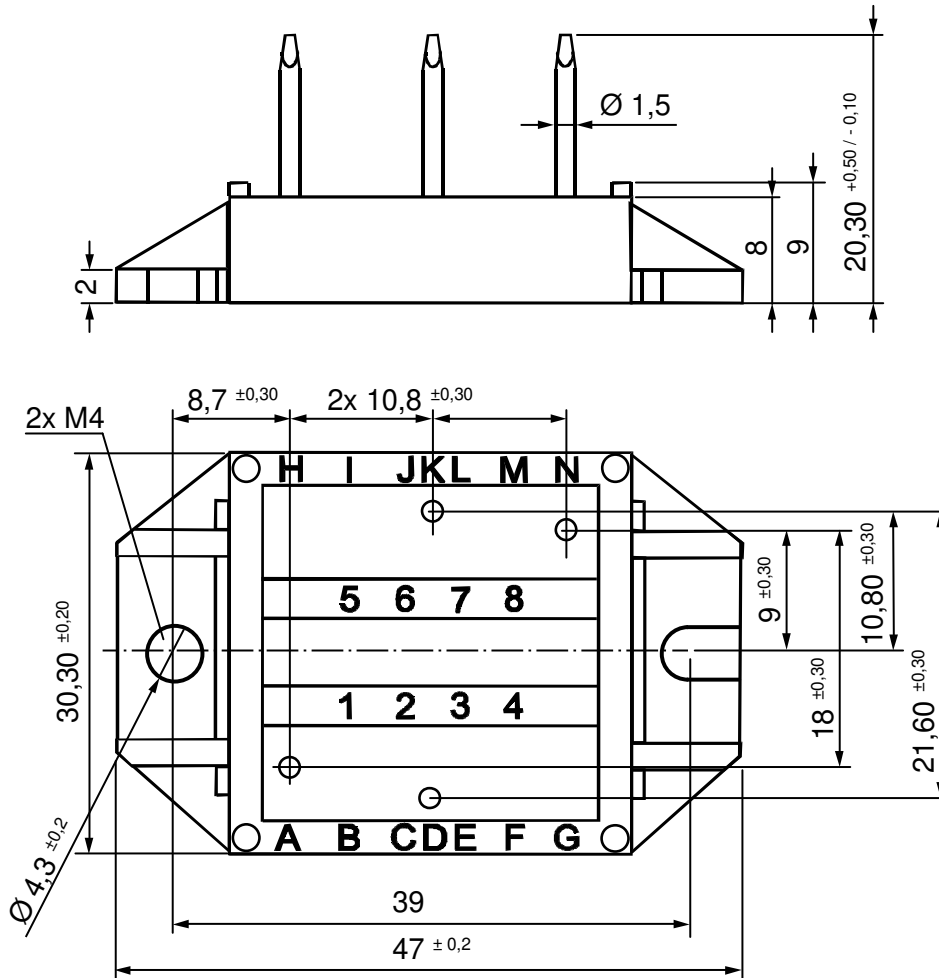


**Fast Diode**

$V_{0\ max}$	threshold voltage	1.32	V
$R_{0\ max}$	slope resistance *	28	mΩ



**Outlines ECO-PAC1**





**Fast Diode**

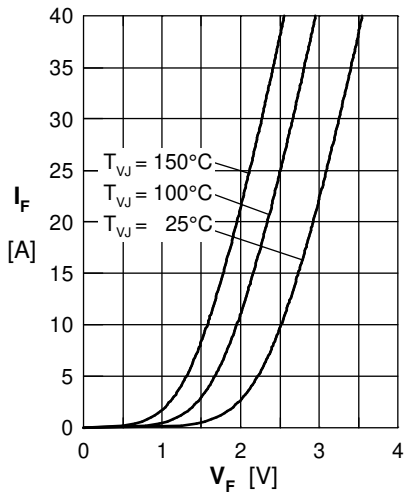


Fig. 1 Forward current  $I_F$  vs.  $V_F$

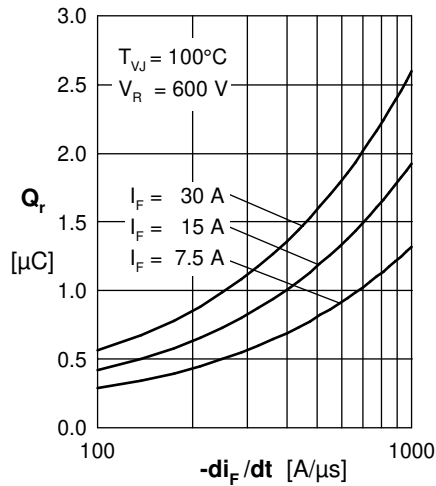


Fig. 2 Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

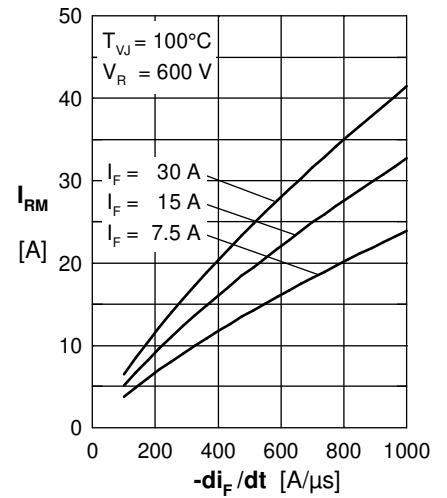


Fig. 3 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

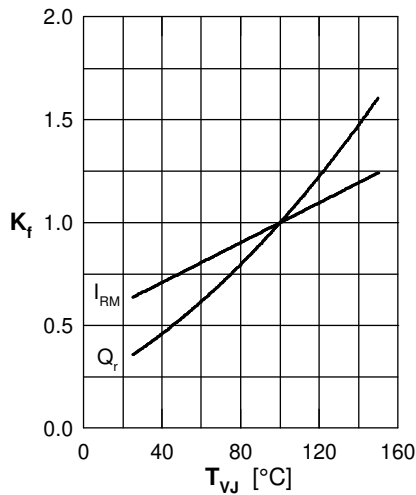


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

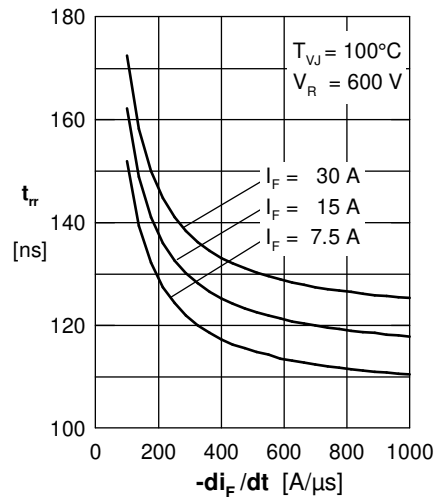


Fig. 5 Recovery time  $t_{tr}$  vs.  $-di_F/dt$

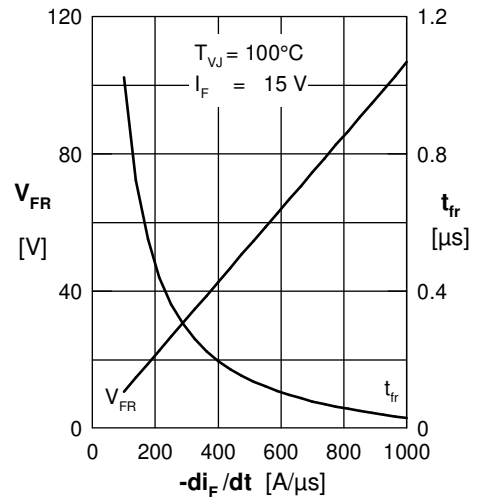


Fig. 6 Peak forward voltage  $V_{FR}$  and  $t_{tr}$  vs.  $-di_F/dt$

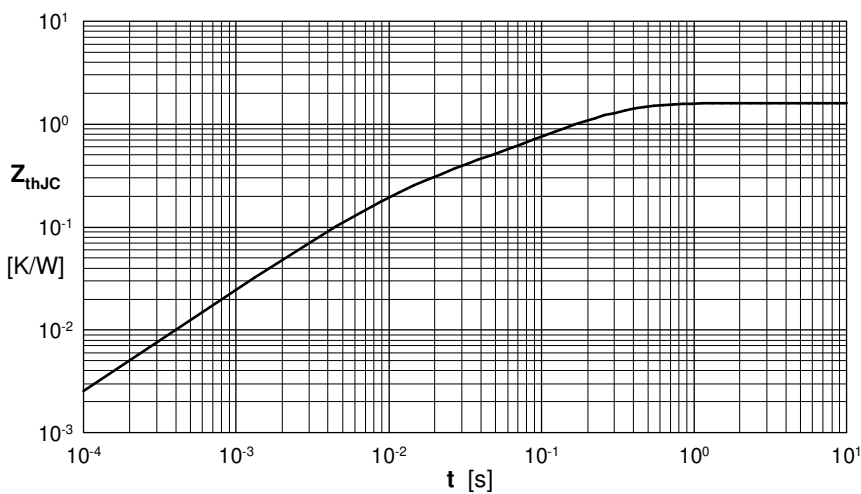


Fig. 7 Transient thermal resistance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.5464	0.0052
2	0.2104	0.0003
3	0.0432	0.0004
4	0.8000	0.0092